

Supporting Information for

Solution-processed copper iodide as an inexpensive and effective anode buffer layer for polymer solar cells

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The UPS of bare ITO, PEDOT/PSS and CuI layers, water contact angle of PEDOT/PSS and CuI layers, AFM images of the three-dimensional structure of ITO and different anode buffer layers, SEM images of CuI films obtained at different rates.

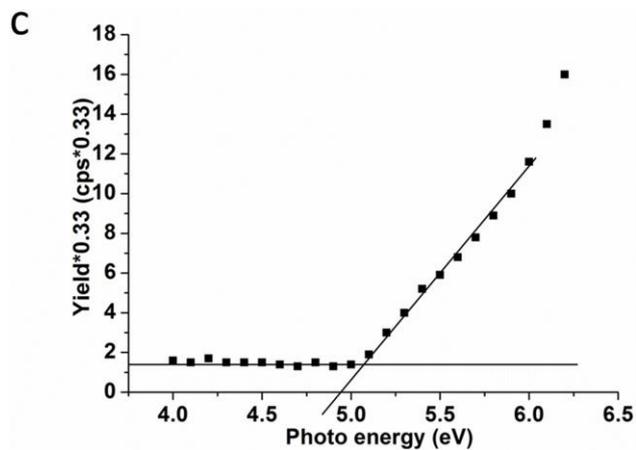
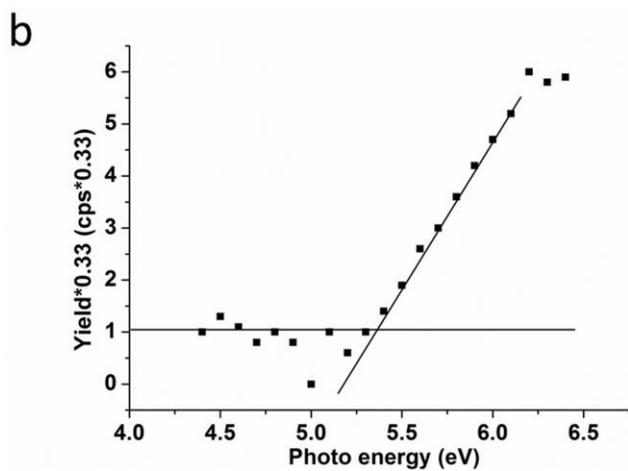
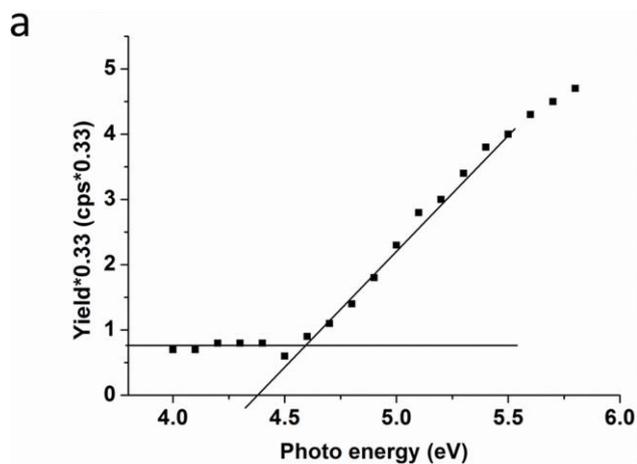


Fig. S1. The ultraviolet photoelectron yield spectroscopy of the different anode interfacial layers: (a) ITO; (b) PEDOT/PSS; (c) CuI-3000.

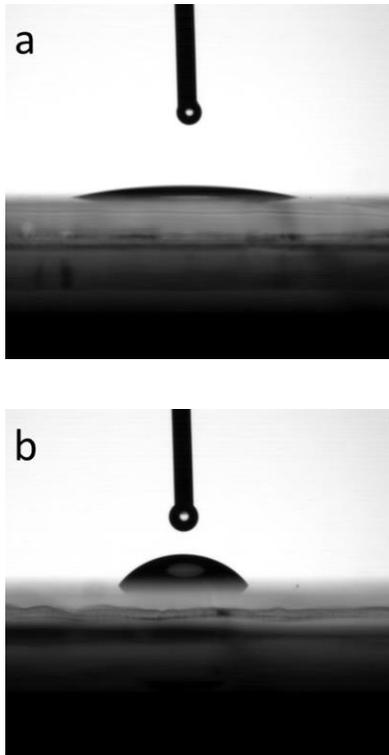
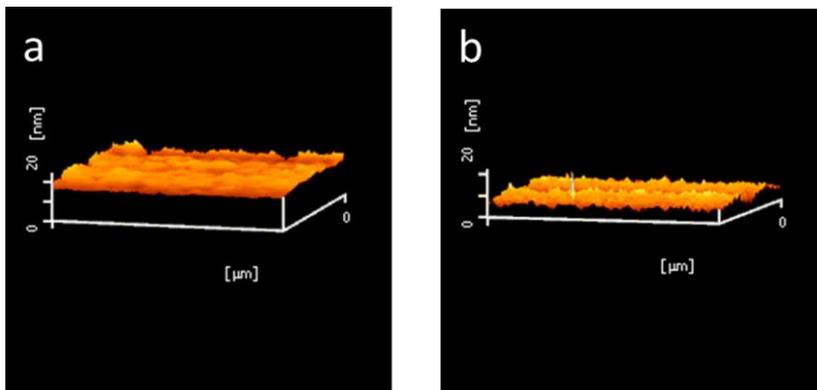


Fig. S2. Water contact angles of (a) PEDOT/PSS on ITO, and (b) CuI-3000 on ITO.



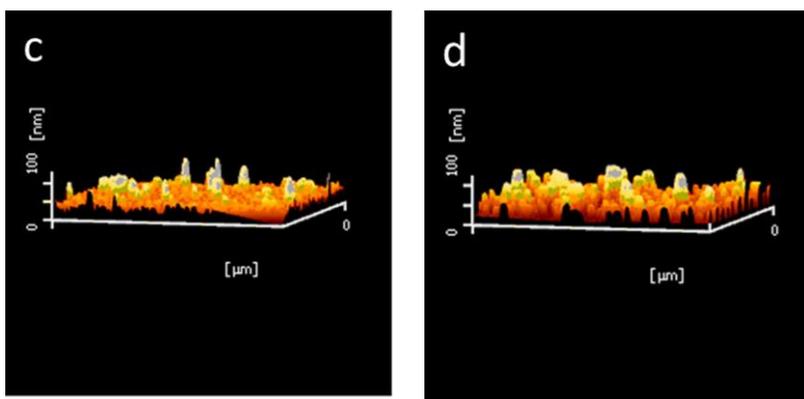


Fig. S3. AFM images of the three-dimensional structure of (a) ITO, (b) ITO/PEDOT/PSS, (c) ITO/CuI-3000 and (d) ITO/a-CuI-3000.

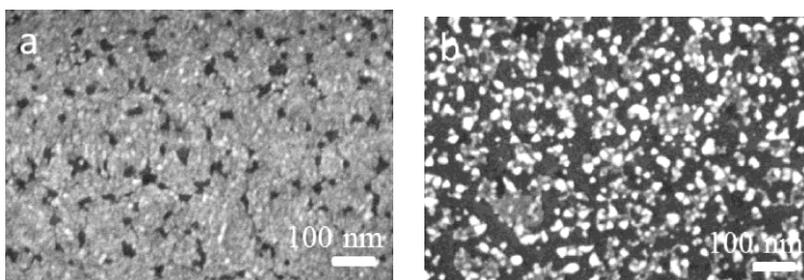


Fig. S4. SEM images in high resolution of CuI films on ITO spin-cast at a low rpm of 1000 (a) and a high rpm of 5000 (b).

Table S1. Pairwise T-tests Comparing the PCE Data of Device B (CuI) and Device D (PEDOT/PSS)

Device	PEDOT/PSS	CuI
Mean	2.820	3.415
Standard Deviation	0.114	0.130
Observations	16	16
df	15	
t	-11.747	
P(T<=t) two-tail	0	

Table S2. Photovoltaic Parameters of PEDOT/PSS and CuI Devices with the Doubled P3HT/PCBM Concentration.

Device	V_{oc} (V)	J_{sc} (mA/cm ²)	FF (%)	PCE (%)	Best PCE (%)
PEDOT/PSS	0.632±0.004	9.20±0.21	46.6±1.0	2.71±0.08	2.83
CuI	0.602±0.008	11.61±0.27	58.2±1.7	4.04±0.12	4.15